



I hereby certify that this correspondence is being deposited with the United States Postal Service as Priority Mail in an Envelope Addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

26 March 2005

Date of Deposit

Graham S. Jones, II; Reg. No. 20,429

Name of Person Making Deposit

Signature

26 March 2005

Date

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventors:	Tina J. Wagner et al.	Date:	26 March 2005
Serial No.:	10/605,100	Art Unit:	2818
Filing Date:	09 September 2003	Examiner:	David Vu
Confirmation No.:	2099	Docket No.:	FIS920030249US1
Title:	Method of Manufacture of Raised Source Drain MOSFET with Top Notched Gate Structure Filled with Dielectric Plug In and Device Manufactured Thereby	Attorney:	Graham S. Jones, II 42 Barnard Avenue Poughkeepsie, NY 12603-5023

AMENDMENT

**The Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

Your Honor:

In response to the Office Action of 1 March 2005, please amend the above-identified application as follows:

Amendments to the Title	begin on page 2 of this paper.
Amendments to the Abstract	begin on page 3 of this paper
Amendments to the Specification	begin on page 4 of this paper
Amendments to the Claims	begin on page 9 of this paper.
Remarks/Arguments	begin on page 14 of this paper.

FIS920030249US1

Serial No.:	10/605,100	Art Unit:	2818
-------------	------------	-----------	------

IN THE TITLE

Please amend the title to read as follows:

~~-- Method of Manufacture of~~ A Raised Source Drain MOSFET with Top Notched Notch Formed on Top of Gate Structure Filled with a Dielectric Plug ~~in and Device Manufactured Thereby --~~